

## ABSTRACT

A thin film capacitance element composition,  
 5 wherein a bismuth layer compound having a c-axis oriented  
 vertically with respect to a substrate surface is  
 expressed by a composition formula of  $(\text{Bi}_2\text{O}_2)^{2+} (\text{A}_{m-1} \text{B}_m \text{O}_{3m+1})^{2-}$  or  $\text{Bi}_2\text{A}_{m-1} \text{B}_m \text{O}_{3m+3}$ , wherein "m" is an even number,  
 "A" is at least one element selected from Na, K, Pb, Ba,  
 10 Sr, Ca and Bi, and "B" is at least one element selected  
 from Fe, Co, Cr, Ga, Ti, Nb, Ta, Sb, V, Mo and W; and Bi  
 in the bismuth layer compound is excessively included  
 with respect to the composition formula of  $(\text{Bi}_2\text{O}_2)^{2+} (\text{A}_{m-1} \text{B}_m \text{O}_{3m+1})^{2-}$  or  $\text{Bi}_2\text{A}_{m-1} \text{B}_m \text{O}_{3m+3}$ , and the excessive content of  
 15 Bi is in a range of  $0 < \text{Bi} < 0.5 \times m$  mol in terms of Bi.